## **ABSTRACT**

Non-oxidizing spacer densification method for producing semiconductor devices, such as MOSFET devices, and that may be implemented during semiconductor fabrication with little or substantially no polycide adhesion loss experienced during spacer densification. The method may be implemented to provide good polycide adhesion characteristics with reduced process complexity over conventional methods by eliminating the need for additional process steps such as metal silicide encapsulation or polysilicon surface treatments.

10

5